IXYS

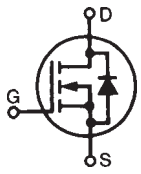
Preliminary Technical Information

Linear Power MOSFET w/Extended FBSOA

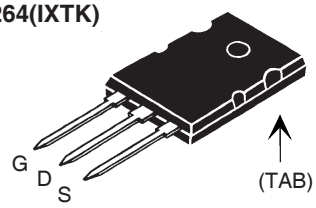
IXTK8N150L
IXTX8N150L

V_{DSS} = 1500V
I_{D25} = 8A
$R_{DS(on)}$ ≤ 3.6Ω

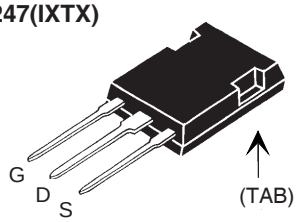
N-Channel Enhancement Mode
Guaranteed FBSOA



TO-264(IXTK)



PLUS247(IXTX)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	1500	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	1500	V
V_{GSS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	T_C = 25°C	8	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	20	A
P_D	T_C = 25°C	700	W
T_J		-55 to +150	°C
T_{JM}		150	°C
T_{stg}		-55 to +150	°C
T_L	1.6mm (0.063 in.) from Case for 10s	300	°C
T_{SOLD}	Plastic Body for 10s	260	°C
M_d	Mounting Torque (IXTK)	1.13/10	Nm/lb.in.
F_C	Mounting Force (IXTX)	20..120 / 4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 1mA	1500			V
$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	5.0		8.0	V
I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V			±200	nA
I_{DSS}	V_{DS} = V_{DSS}			50	μA
	V_{GS} = 0V, T_J = 125°C			3	mA
$R_{DS(on)}$	V_{GS} = 20V, I_D = 0.5 • I_{D25}, Note 1			3.6	Ω

Features

- Designed for Linear Operations
- International Standard Packages
- Guaranteed FBSOA at 60°C
- Molding Epoxies Meet UL94 V-0 Flammability Classification

Applications

- Programmable Loads
- Current Regulators
- DC-DC Convertors
- Battery Chargers
- DC Choppers
- Temperature and Lighting Controls

Advantages

- Easy to Mount
- Space Savings
- High Power Density

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Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 50V, I_D = 0.5 • I_{D25}, Note 1	1.4	2.3	3.2	S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		8000		pF
C_{oss}			405		pF
C_{rss}			70		pF
$t_{d(on)}$	**Resistive Switching Times**		36		ns
t_r	V_{GS} = 15V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		18		ns
$t_{d(off)}$	R_G = 2Ω (External)		90		ns
t_f			95		ns
$Q_{g(on)}$	V_{GS}= 15V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		250		nC
Q_{gs}			80		nC
Q_{gd}			116		nC
R_{thJC}				0.18	°C/W
R_{thCS}			0.15		°C/W

Safe Operating Area Specification

Symbol	Test Conditions	Characteristic Values Min.	Typ.	Max.	
SOA	V_{DS} = 1000V, I_D = 0.5A, T_C = 60°C, T_P = 3s	500			W

Source-Drain Diode

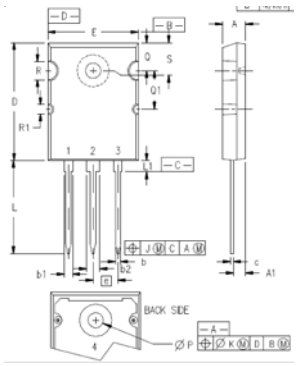
Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			8	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			32	A
V_{SD}	I_F = 8A, V_{GS} = 0V, Note 1			1.2	V
t_{rr}	I_F = I_S, -di/dt =100A/μs, V_R = 100V		1700		ns

Notes: 1. Pulse Test, t ≤ 300μs; Duty Cycle, d ≤ 2%.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

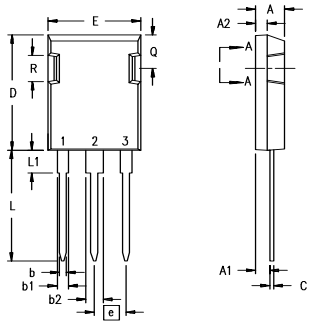
TO-264 (IXTK) Outline



1 – GATE
2, 4 – DRAIN (COLLECTOR)
3 – SOURCE (EMITTER)

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

PLUS 247™ (IXTX) Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.83	5.21	.190	.205
A_1	2.29	2.54	.090	.100
A_2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b_1	1.91	2.13	.075	.084
b_2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,850,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Extended Output Characteristics @ 25ºC

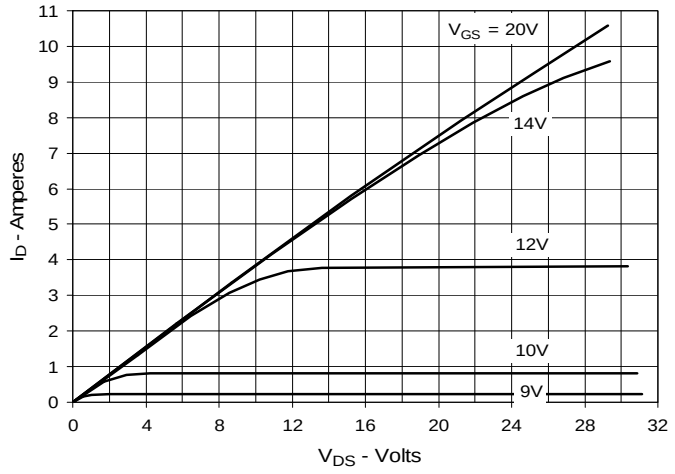


Fig. 2. Output Characteristics @ 125ºC

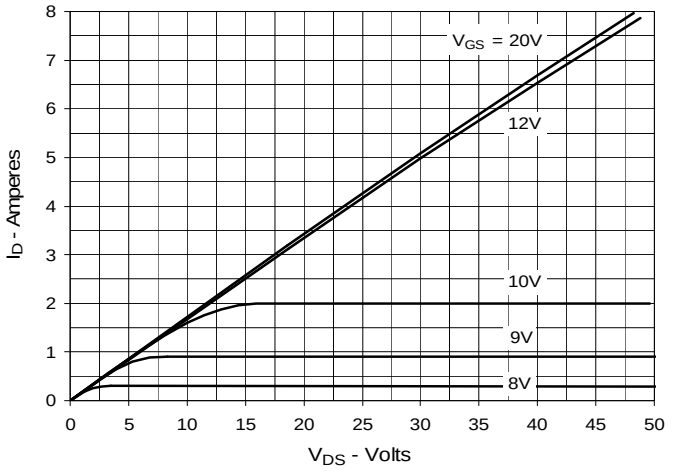


Fig. 3. $R_{DS(on)}$ Normalized to I_D = 4A Value vs. Junction Temperature

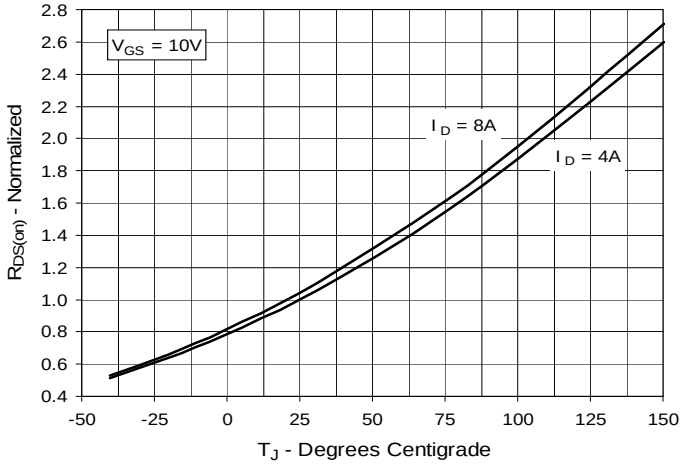


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 4A Value vs. Drain Current

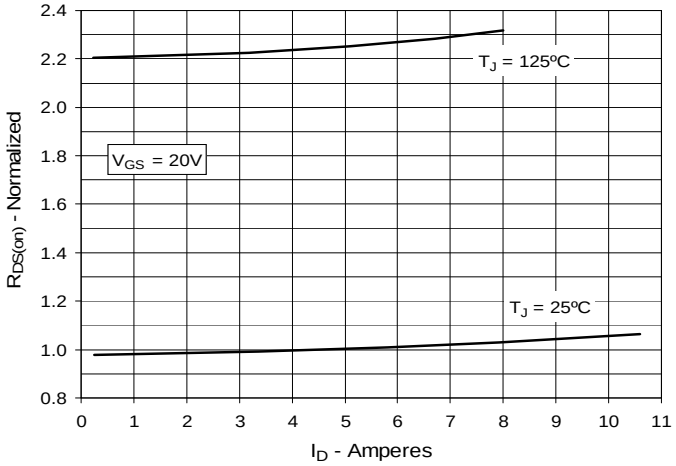


Fig. 5. Maximum Drain Current vs. Case Temperature

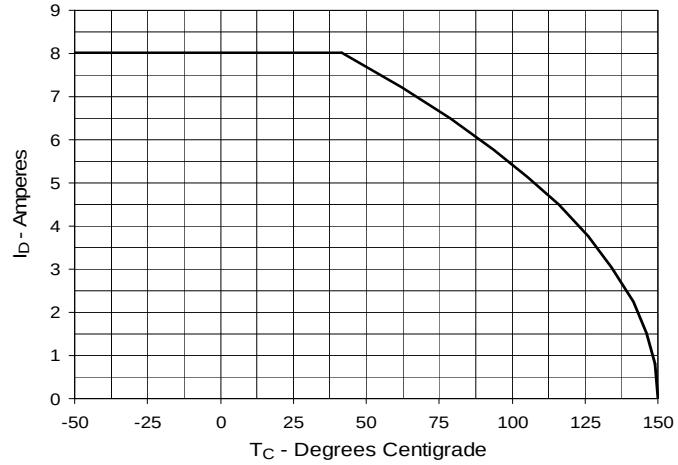


Fig. 6. Input Admittance

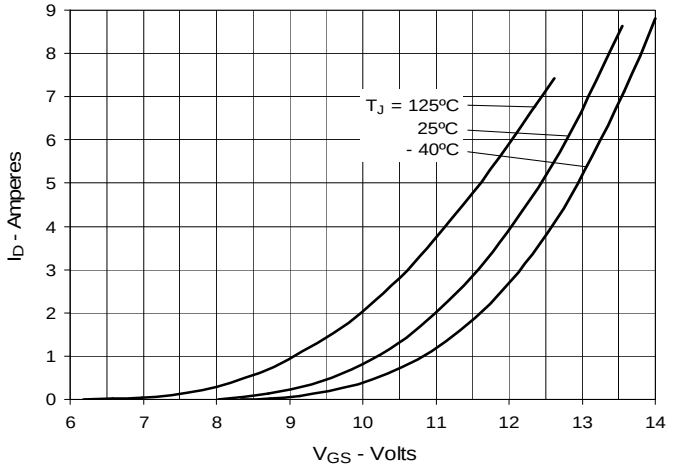


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Fig. 7. Transconductance

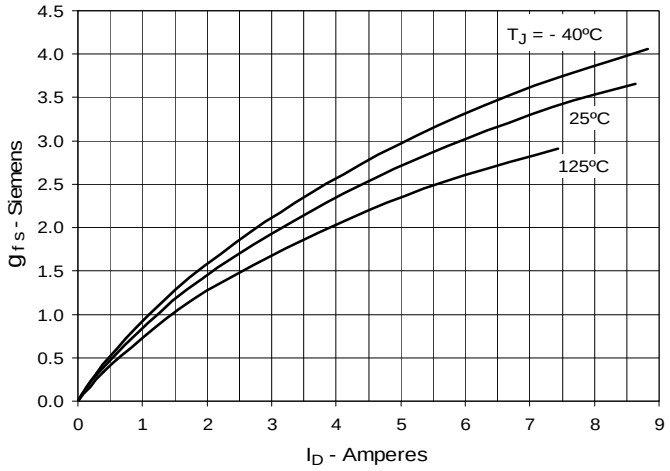

Fig. 8. Forward Voltage Drop of Intrinsic Diode

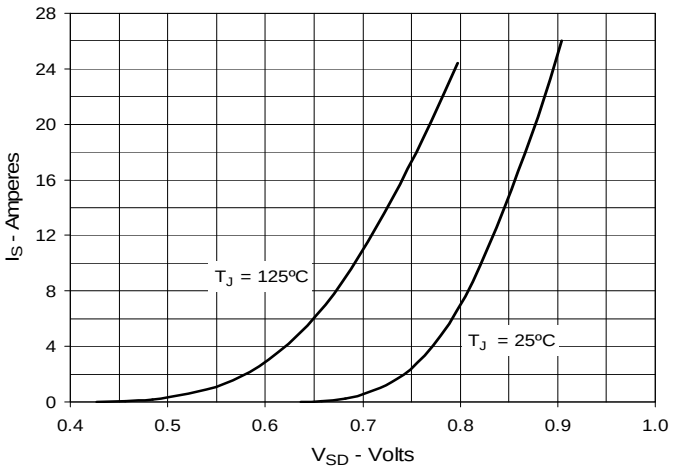

Fig. 9. Gate Charge

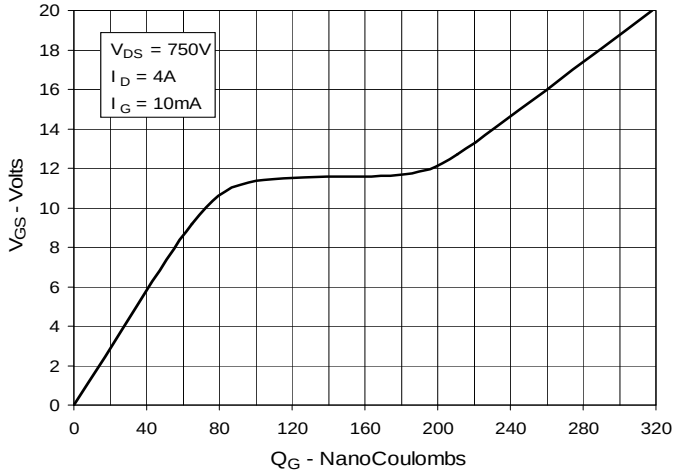

Fig. 10. Capacitance

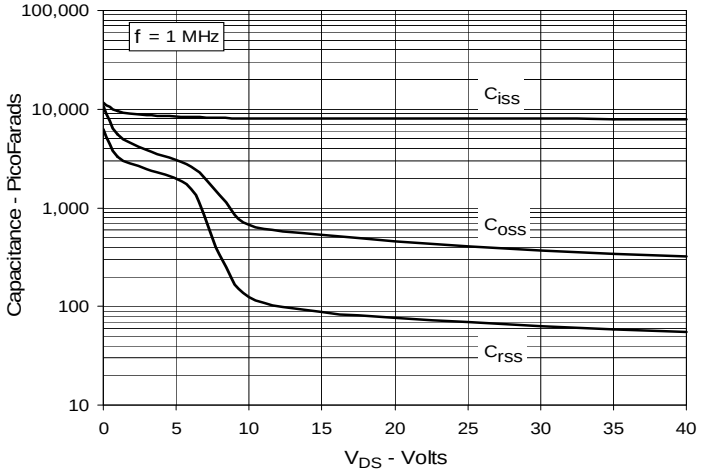

Fig. 11. Maximum Transient Thermal Impedance

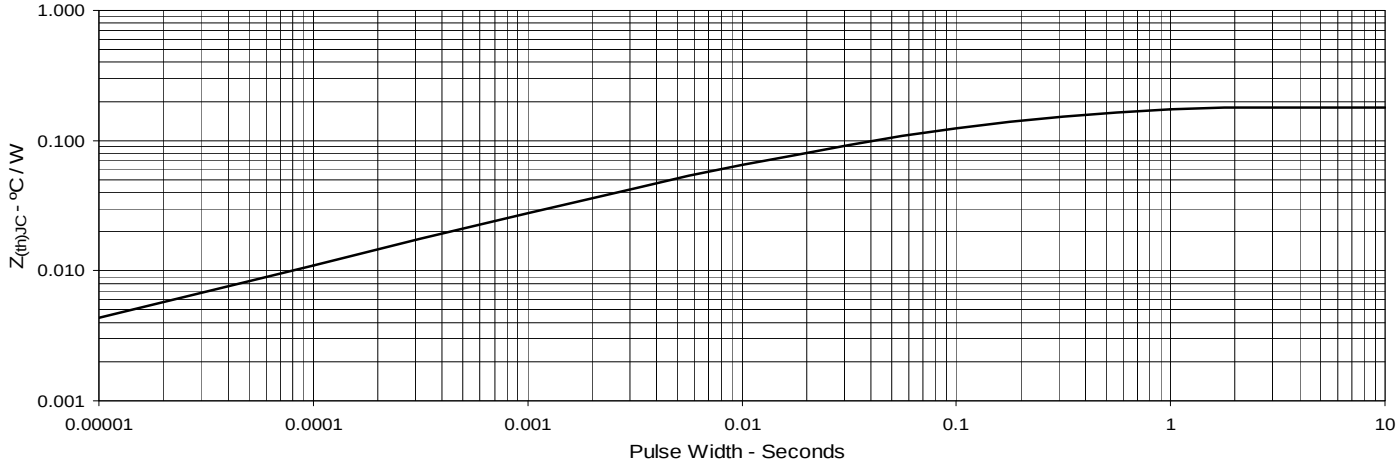

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Fig. 12. Forward-Bias Safe Operating Area @ T_C = 25ºC

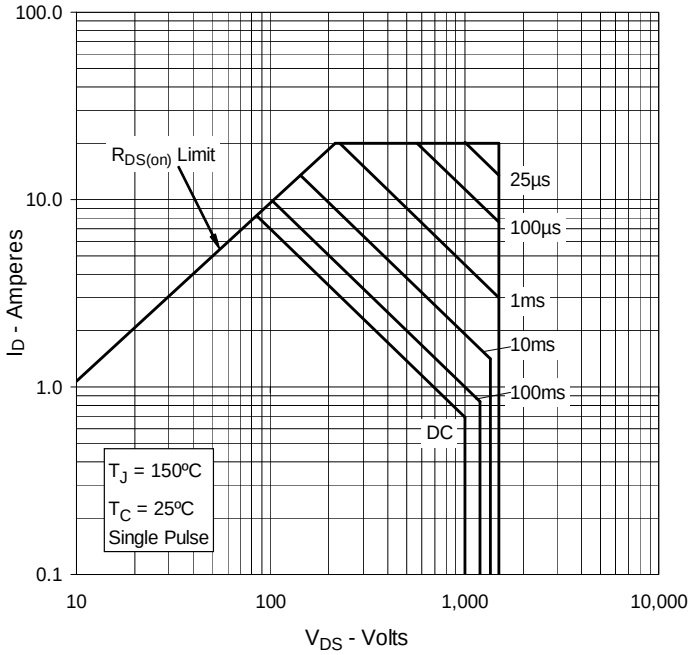
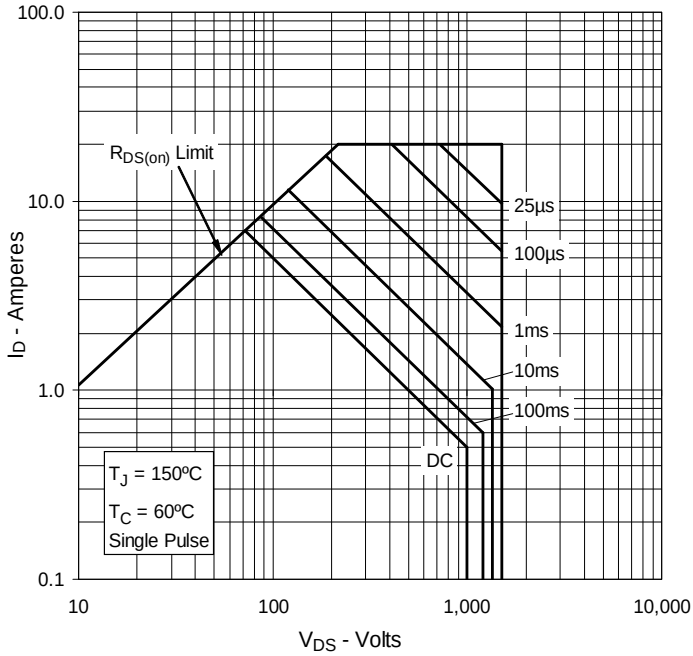


Fig. 13. Forward-Bias Safe Operating Area @ T_C = 60ºC



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